



## **TO-9 Packaged Laser Diode**

High Power Single-Mode and Multi-Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

- ApplicationsOEM MedicalProfessional Medical

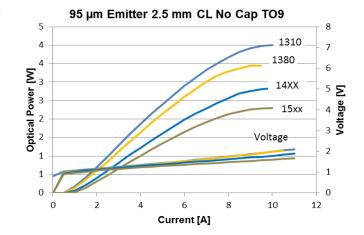
- LiDAR
  Military / Aerospace
  Illumination

## Features

- Cost effective
- High Output Power High Dynamic Range •
- •
- High Efficiency
- Standard Low Cost Package

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements. requirements.





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PI Sheet





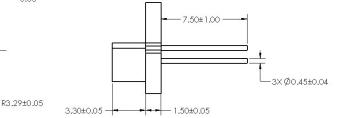
SemiNex
LASER DIODES

	Symbol	TO9-184	Units
Optical			
Wavelength	λ <sub>c</sub>	1310	nm (±20)
Output Power (<10ns)	P°	42.00	watts (±10%)
Output Power (150ns)	P	20.00	watts (±10%)
Chip Cavity Length	CL	2500	μm
No. of Junctions		1	
Emitter Width	W	95	μm
Emitter Height	Н	1	μm
Spectral Width	δλ	10	nm 3dB
Slope Efficiency	η°	0.35	W/A
Fast Axis Div.*	O_perp	28	deg FWHM
Slow Axis Div.	O_parallel	10	deg FWHM
Electrical			
Power Conversion Eff.	η	5	%
Operating Current (<10ns)	I <sub>op</sub>	120	A
Operating Current (150ns)	I <sub>op</sub>	60	A
Threshold Current	I <sub>th</sub>	0.5	A
Operating Voltage	V <sub>op</sub>	6.2	V
Mechanical			
Weight		1.5	g
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

Specified values are rated at a constant heat sink temperature of 20°C.
\*\*Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.
Uncapped TO9 specifications assume heatsinking underneath laser chip.
Capped TO9 specifications assume heatsinking only on flat surface where pins extend.

1.00±0.05 R0.15 MAX SUBMOUNT TO-9 EDGE 0.100±0.045 0.000 WIRE BONDS DETAIL B SCALE 16 : 1 ₹o AIN SUBMOUNT TO WIRE LEAD 0.40±0.05 AIN SUBMOUNT-LASER DIE LASER DIE/TO-9 CENTERLINE ALIGNMENT 0.000 ±0.010 HI 0.40±0.05 mm 90.00° 010 LASER DIE FRONT FACET SUBMOUNT ALIGNMENT R0.30±0.05 DETAIL C SC ALE 10 : 1 0.000±0.030 WIRE BONDS -BACK TO LASER DIE TO WIRE LEAD DETAIL A SCALE 16:1 13X 2mil WIRE BONDS Ø9.00\_0.00 Ø2.54±0.05 7.50±1.00 O Ð PIN OUT:

> LD CATHODE ( - ) CASE LD ANODE ( + ) 1. 2. 3.





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